

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

GP/1765  
\$

Application of

Jason M. Benz

Serial No.: 09/695,028

Group Art Unit: 1765

Filed: October 24, 2000

Examiner: Alanko, Anita K.

For: METHOD FOR THIN FILM LASER REFLECTANCE CORRELATION FOR  
SUBSTRATE ETCH ENDPOINT

**EXCESS CLAIM FEE PAYMENT LETTER**

Sir:


Transmitted herewith is an amendment in the above-identified application. The fee has been calculated and is transmitted as shown below.

	<u>AFTER AMENDMENT</u>	<u>PREV. PAID FOR</u>	<u>EXTRA CLAIMS PRESENT</u>	<u>RATE</u>	<u>FEE DUE</u>
Total Claims	33 -	30	= 3	x \$18.00	\$ 54.00
Indep. Claims	3 -	3	= 0	x \$84.00	\$ .00
<b>TOTAL ADDITIONAL FEE FOR THIS AMENDMENT</b>					<b>\$ 54.00</b>

Please charge Assignee's Deposit Account No. 09-0456 in the amount of \$ 54.00 to cover the excess claim fees. A duplicate copy of this sheet is enclosed. The Commissioner is authorized to charge any deficiencies in fees and credit any overpayment of fees to Assignee's Deposit Account No. 09-0456.

Respectfully Submitted,

Date: 10/8/02

  
Sean M. McGinn  
Reg. No. 34,386

**McGinn & Gibb, PLLC**  
Intellectual Property Law  
8321 Old Courthouse Rd. Suite 200  
Vienna, VA 22182-3817  
(703) 761-4100  
Customer No. 21254

RECEIVED  
OCT 10 2002  
TC 1700 MAIL ROOM



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#9/B  
na  
10/5/02

In re Application of

Jason M. Benz

Serial No.: 09/695,028

Group Art Unit: 1765

Filed: October 24, 2000

Examiner: Alanko, Anita K.

For: METHOD FOR THIN FILM LASER REFLECTANCE CORRELATION FOR  
SUBSTRATE ETCH ENDPOINT

Honorable Commissioner of Patents  
Washington, D.C. 20231

RECEIVED  
OCT 10 2002  
TC 1700 MAIL ROOM

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated July 8, 2002, please amend the above-identified  
application as follows:

IN THE CLAIMS:

10/10/2002 EHAILE1 00000028 090456 09695028  
01 FC:103 54.00 CH

Please amend the claims as follows:

B1  
1 (Amended) A method of etching a substrate, comprising:  
2 measuring a reflectance signal from a reflective material deposited on said substrate as  
3 the substrate is being etched;  
4 correlating the substrate etch rate to the reflectance signal from the reflective material;  
5 and  
6 using the etch relation between the substrate and the reflective material to determine  
7 the etch target,  
8 wherein said reflective material is isolated from an etching process.

B2D3  
1 (Amended) The method of claim 1, wherein said reflective material comprises metal  
having a metal oxide thereon, and said substrate etch also etches said metal oxide on said